

SKT 55, SKT 80, SKT 100

| V_{RSM} | V_{RRM} V_{DRM} | $(dv/dt)_{cr}$ | I_{TRMS} (maximum values for continuous operation) | | |
|-----------|------------------------|----------------|--|---------------------|----------------------|
| | | | 110 A | 135 A | 175 A |
| V | V | V/ μ s | I_{TAV} (sin. 180; $T_{case} = 80$ °C) | | |
| | | | 70 A | 86 A | 110 A |
| 500 | 400 | 500 | SKT 55/04 D | – | SKT 100/04 D |
| 700 | 600 | 500 | SKT 55/06 D | SKT 80/06 D* | – |
| 900 | 800 | 500 | SKT 55/08 D | SKT 80/08 D | SKT 100/08 D* |
| 1300 | 1200 | 1000 | SKT 55/12 E | SKT 80/12 E* | SKT 100/12 E* |
| 1500 | 1400 | 1000 | SKT 55/14 E | SKT 80/14 E | SKT 100/14 E* |
| 1700 | 1600 | 1000 | SKT 55/16 E | SKT 80/16 E | SKT 100/16 E* |
| 1900 | 1800 | 1000 | SKT 55/18 E♦ | SKT 80/18 E♦ | SKT 100/18 E♦ |

Thyristors

SKT 55 SKT 80 SKT 100



| Symbol | Conditions | SKT 55 | SKT 80 | SKT 100 | Units |
|---------------------|---|-------------------|---------------------|------------------|--------------------------------------|
| I_{TAV} | sin. 180; ($T_{case} = \dots$) | 55 (92) | 80 (85) | 100 (85) | A °C |
| I_{TSM} | $T_{vj} = 25$ °C; 10 ms $T_{vj} = 130$ °C; 10 ms | 1 300 1 100 | 1 700 1 500 | 2 000 1 750 | A A |
| i^2t | $T_{vj} = 25$ °C; 8,35 ... 10 ms $T_{vj} = 130$ °C; 8,35 ... 10 ms | 8 500 6 000 | 14 500 11 000 | 20 000 15 000 | A ² s A ² s |
| t_{gd} | $T_{vj} = 25$ °C $I_G = 1$ A $di_G/dt = 1$ A/ μ s | typ. 1 | | | μ s |
| t_{gr} | $V_D = 0,67 \cdot V_{DRM}$ | typ. 2 | | | μ s |
| $(di/dt)_{cr}$ | $f = 50 \dots 60$ Hz | 50 | | | A/ μ s |
| I_H | $T_{vj} = 25$ °C; typ./max. | 150 / 250 | | | mA |
| I_L | $T_{vj} = 25$ °C; typ./max. | 300 / 600 | | | mA |
| t_q | $T_{vj} = 130$ °C; typ. | 100 | | | μ s |
| V_T | $T_{vj} = 25$ °C; ($I_T = \dots$); max. | 1,8 (200) | 2,25 (300) | 1,75 (300) | V A |
| $V_{T(TO)}$ | $T_{vj} = 130$ °C | 0,9 | 1,2 | 1,0 | V |
| r_T | $T_{vj} = 130$ °C | 4 | 4 | 2,4 | m Ω |
| I_{DD} ; I_{RD} | $T_{vj} = 130$ °C; $V_{RD} = V_{RRM}$ $V_{DD} = V_{DRM}$ | 25 | 30 | 30 | mA |
| V_{GT} | $T_{vj} = 25$ °C | 3 | | | V |
| I_{GT} | $T_{vj} = 25$ °C | 150 | | | mA |
| V_{GD} | $T_{vj} = 130$ °C | 0,25 | | | V |
| I_{GD} | $T_{vj} = 130$ °C | 10 | | | mA |
| R_{thjc} | cont. sin. 180 / rec. 120 | 0,40 0,47/0,53 | 0,25 0,28 / 0,31 | | °C/W °C/W |
| R_{thch} | | 0,08 | | | °C/W |
| T_{vj} | | – 40 ... + 130 | | | °C |
| T_{stg} | | – 40 ... + 150 | | | °C |
| M | SI units US units | 10 90 | | | Nm lb. in. |
| a | | 5 · 9,81 | | | m/s ² |
| w | | 65 | 80 | | g |
| Case | | B 5 | | | |

* Available with UNF thread 1/2-20 UNF2A, e.g. SKT 80/06 D UNF

♦ Available in limited quantities

Features

- Hermetic metal cases with ceramic insulators
- Threaded studs ISO M12 or UNF 1/2-20
- Interchangeable with international standard cases

Typical Applications

- DC motor control (e. g. for machine tools)
- Controlled rectifiers (e. g. for battery charging)
- AC controllers (e. g. for temperature control)

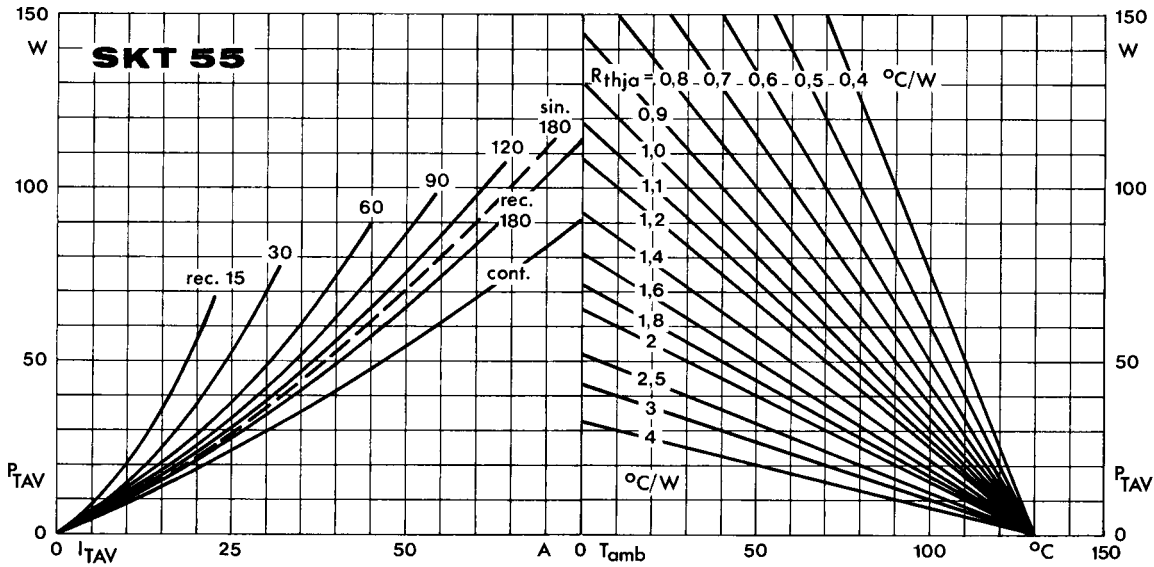


Fig. 1 a Power dissipation vs. on-state current and ambient temperature

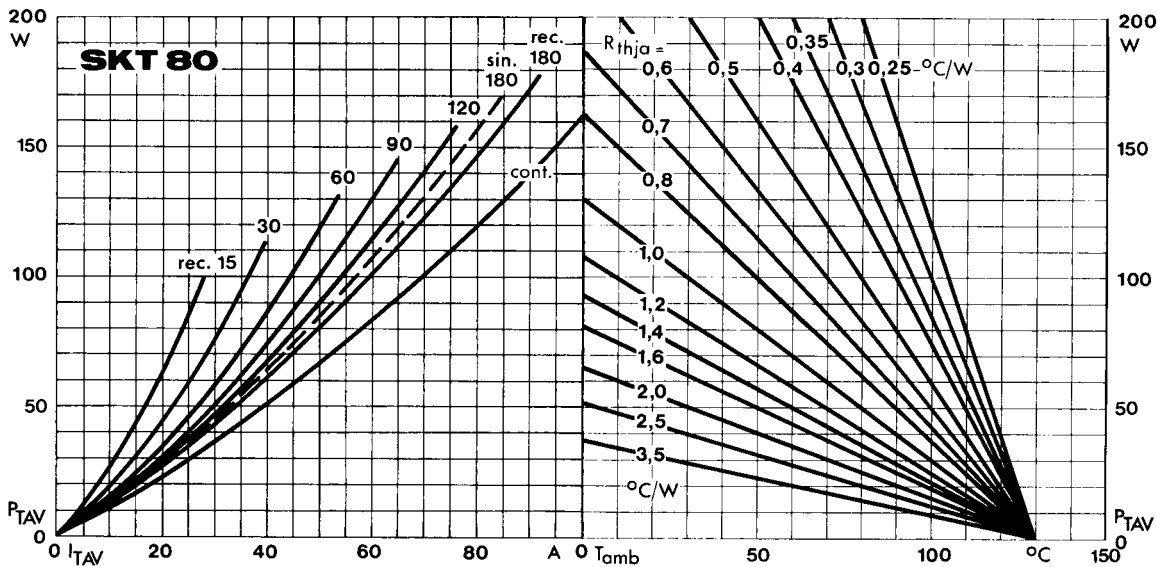


Fig. 1 b Power dissipation vs. on-state current and ambient temperature

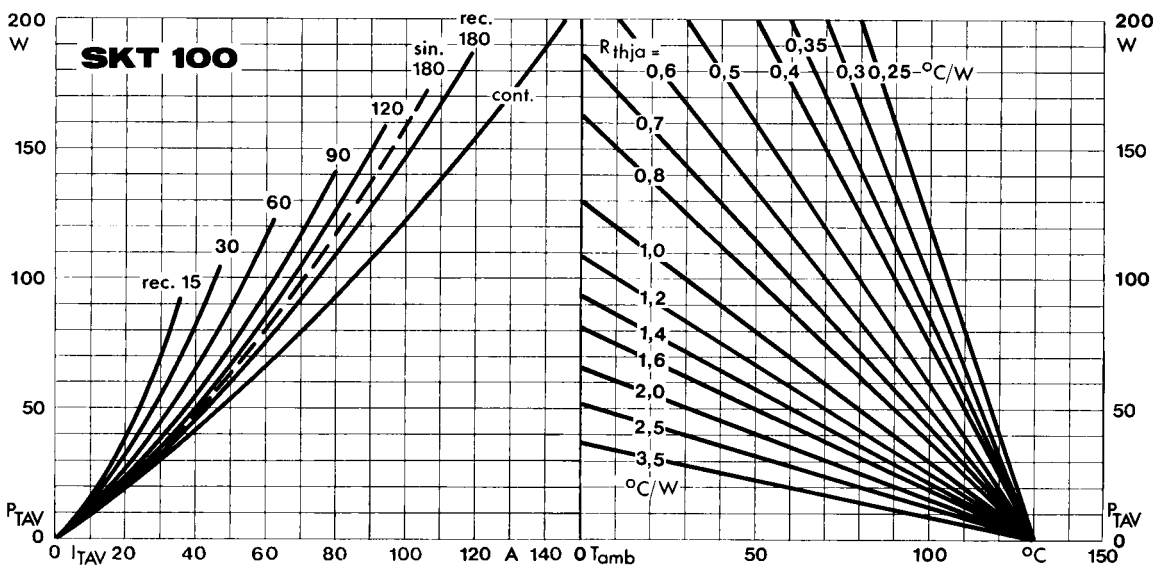


Fig. 1 c Power dissipation vs. on-state current and ambient temperature

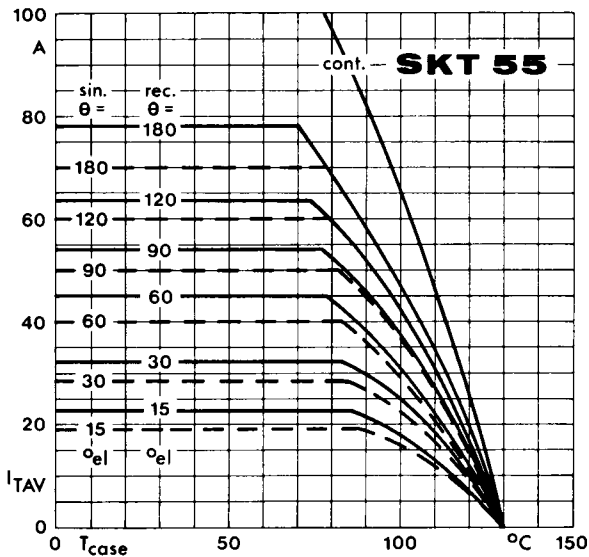


Fig. 2 a Rated on-state current vs. case temperature

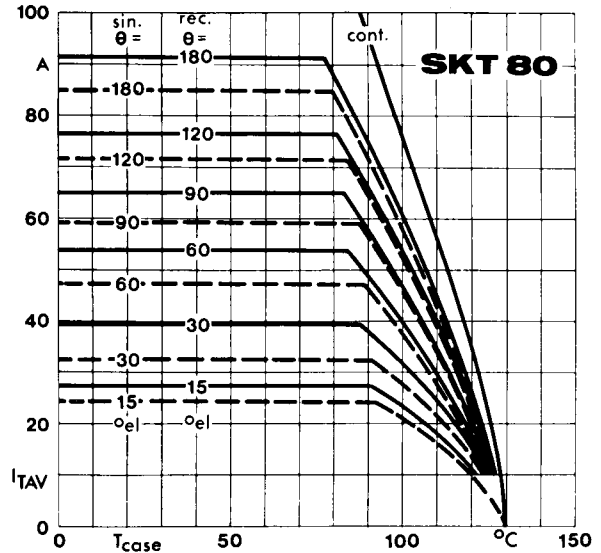


Fig. 2 b Rated on-state current vs. case temperature

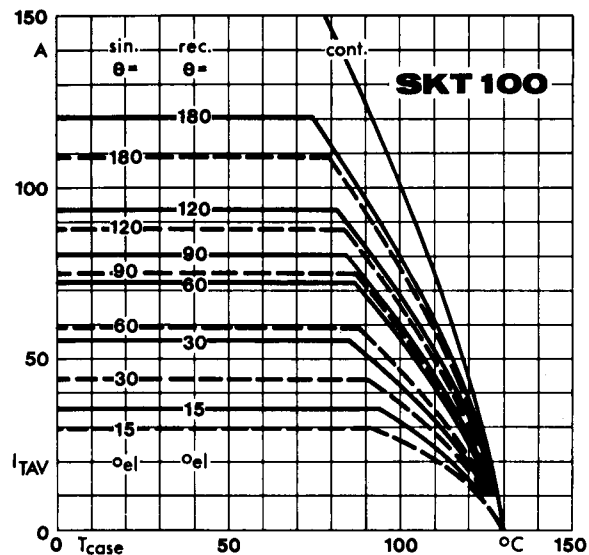


Fig. 2 c Rated on-state current vs. case temperature

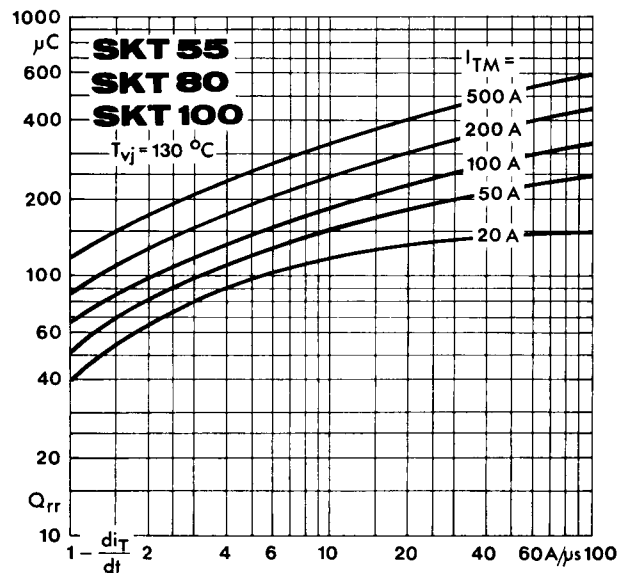


Fig. 3 Recovered charge vs. current decrease

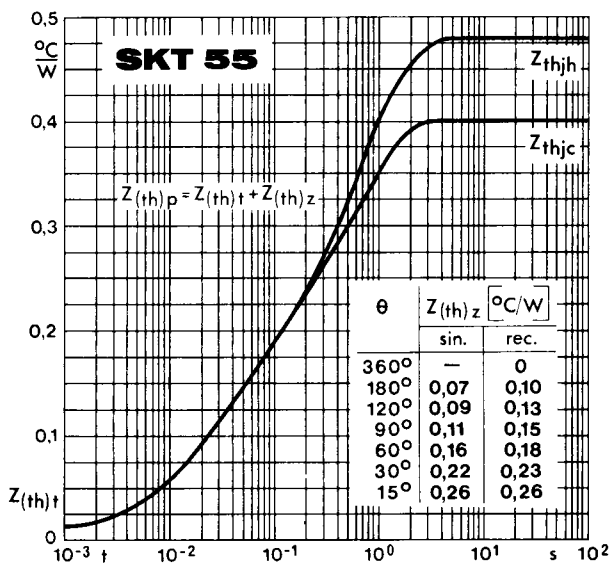


Fig. 4 a Transient thermal impedance vs. time

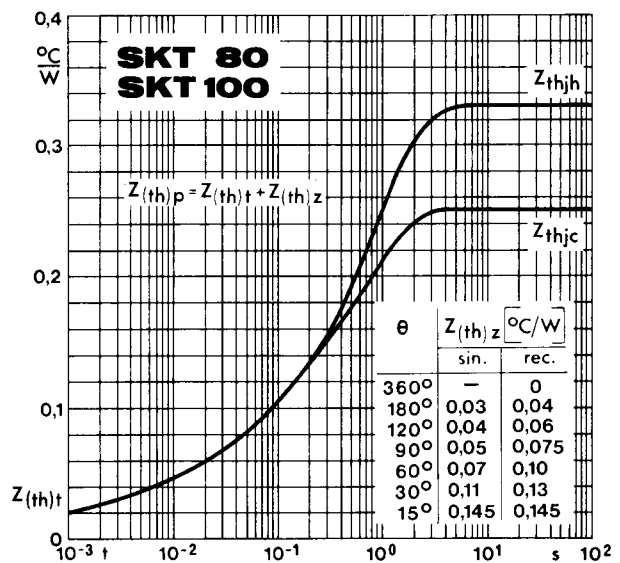


Fig. 4 b Transient thermal impedance vs. time

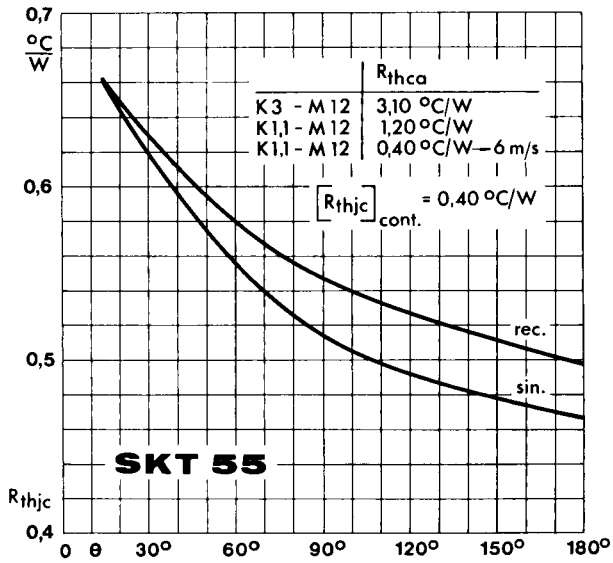


Fig. 5 a Thermal resistance vs. conduction angle

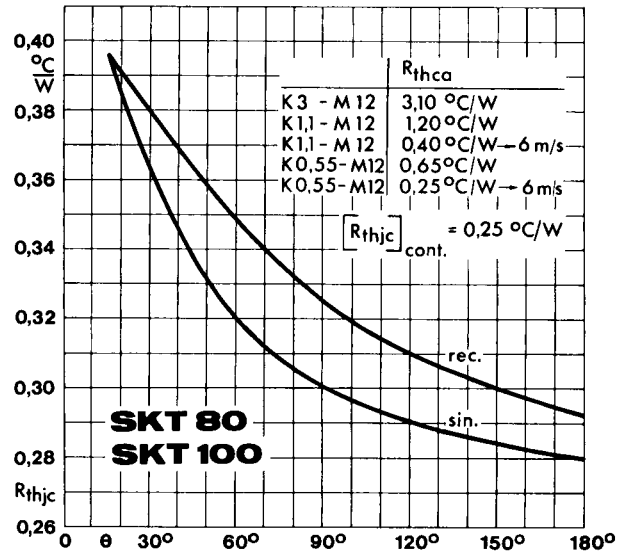


Fig. 5 b Thermal resistance vs. conduction angle

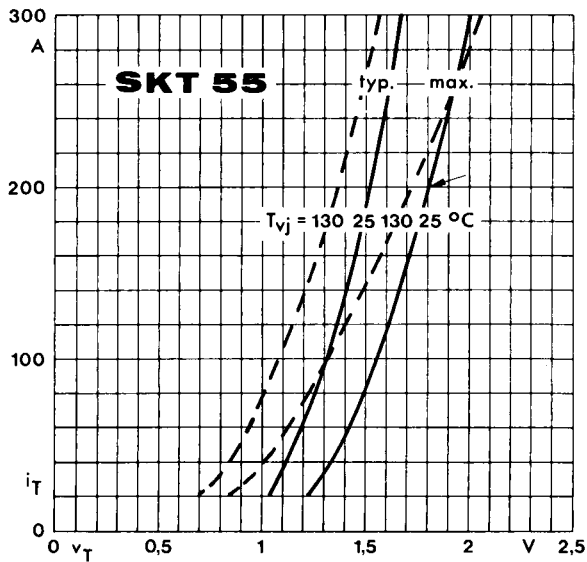


Fig. 6 a On-state characteristics

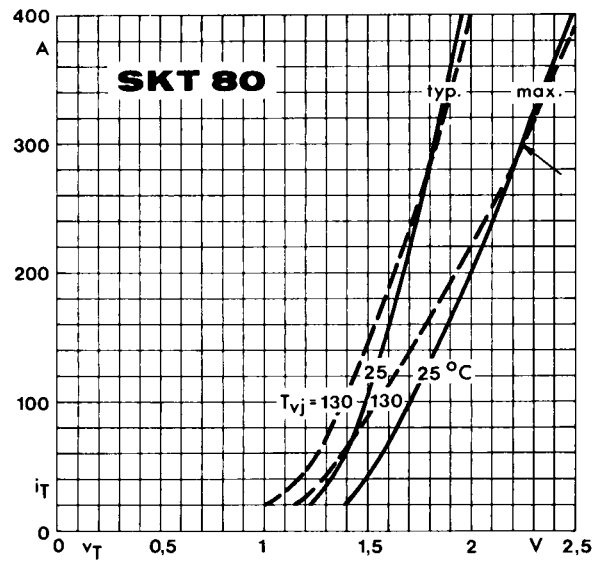


Fig. 6 b On-state characteristics

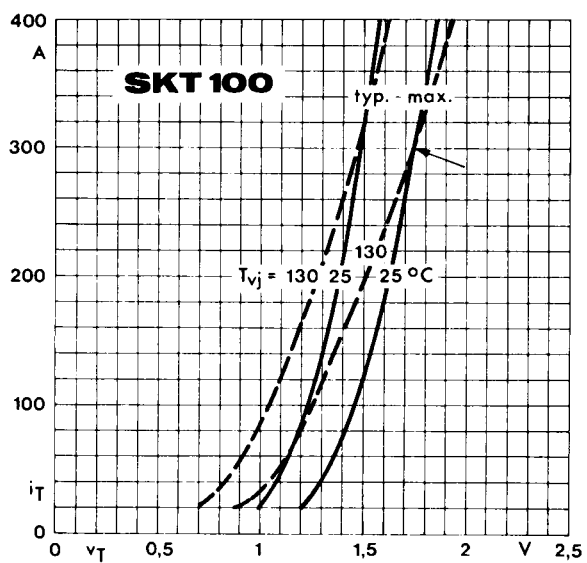


Fig. 6 c On-state characteristics

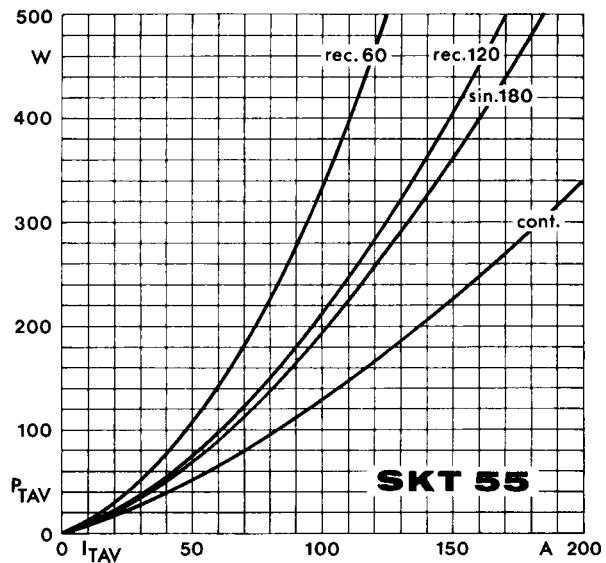


Fig. 7 a Power dissipation vs. on-state current

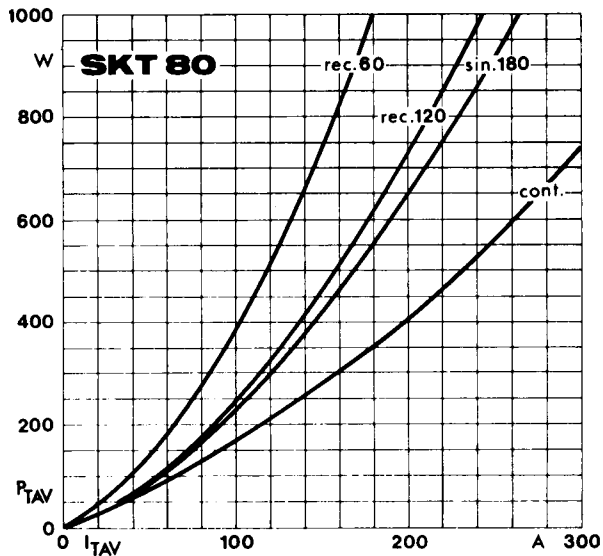


Fig. 7 b Power dissipation vs. on-state current

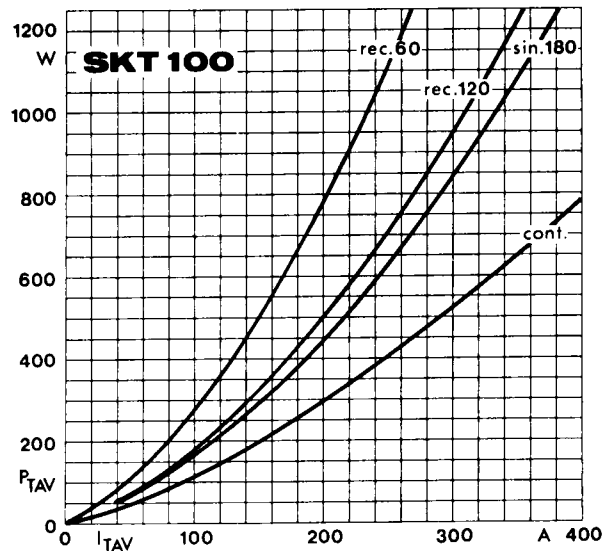


Fig. 7 c Power dissipation vs. on-state current

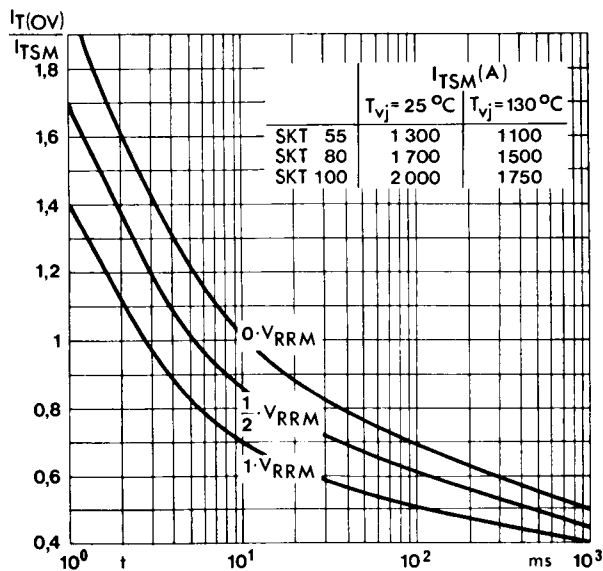


Fig. 8 Surge overload current vs. time

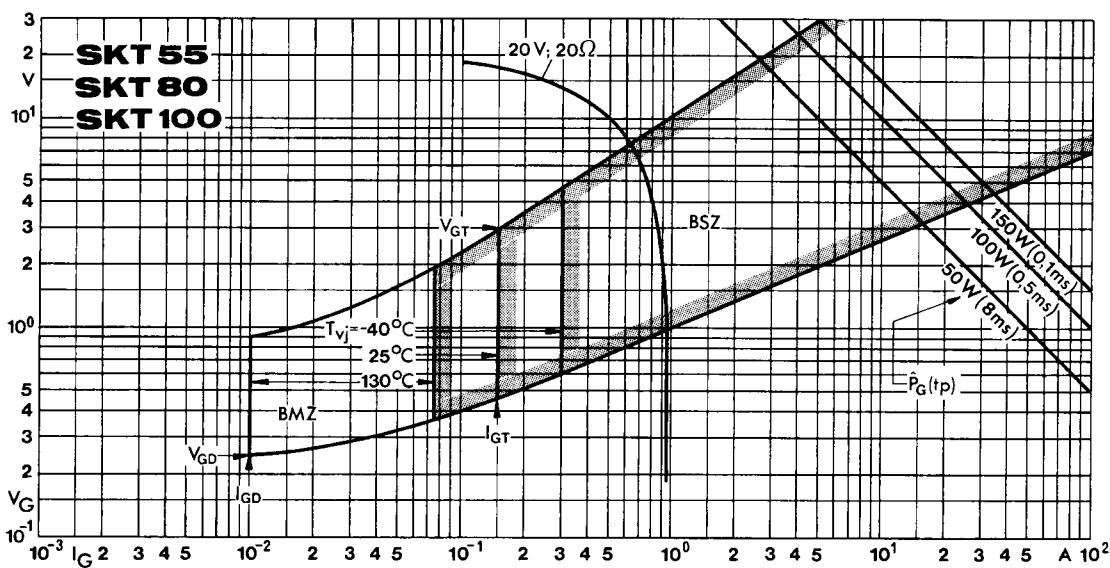


Fig. 9 Gate trigger characteristics

**SKT 55
SKT 80
SKT 100**

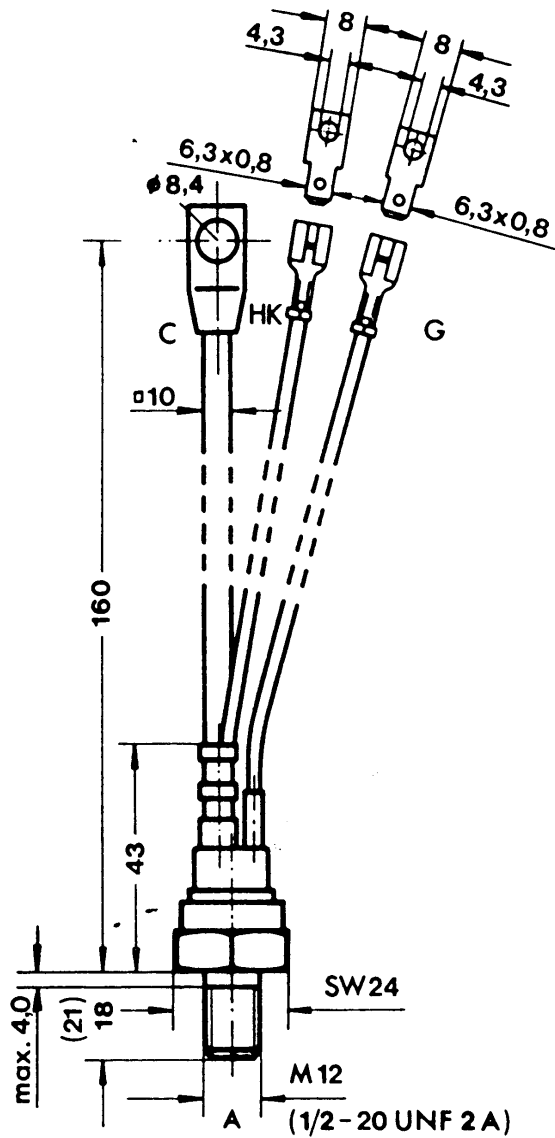
Case B 5

IEC-Publ. 191-2: (A 12 MA, A 12 U)

DIN 41892: (204 B 3)

BS 3934: SO - 30 C

JEDEC: TO - 209 (TO - 94)¹⁾



¹⁾ modified version. In the USA and Canada these types are available with the original TO-209 (TO-94) dimensions. TO-208 AD (TO-83) with flag terminals is also available.

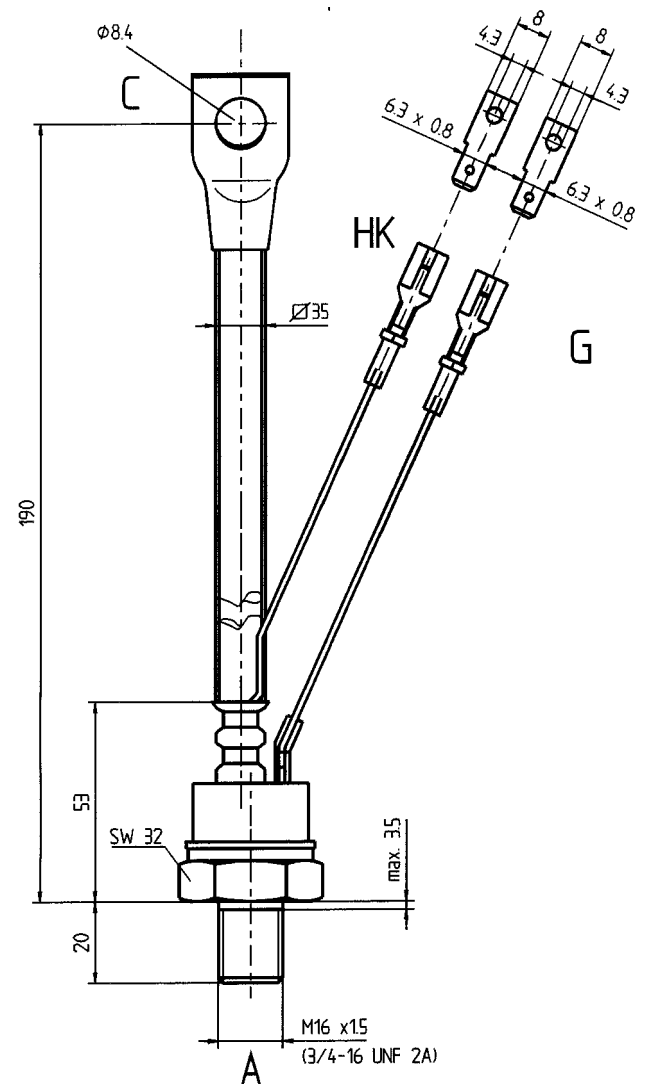
**SKT 130
SKT 160**

Case B 6

IEC-Publ. 191-2: A 47 MC

DIN 41893: 205 B 4

JEDEC: TO-209 (TO-93)



Dimensions in mm

- C: Cathode terminal (red sleeve)
- A: Anode terminal
- G: Gate terminal (yellow sleeve)
- HK: Auxiliary cathode terminal (red sleeve)